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N-Channel 80 V (D-S) Super Junction Power MOSFET

PRODUCT SUMMARY							
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A)	Q _g (TYP.)				
80	0.0021 at V _{GS} = 10 V	200	168 nC				
	0.0027 at V _{GS} = 4.5 V	180	100110				

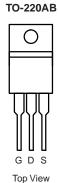
FEATURES

- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested



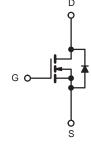
APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Battery management



Din-Tek

SEMICONDUCTOR



N-Channel MOSFE

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	80	V	
Gate-Source Voltage		V _{GS}	± 20	V	
Outline Print Outline 450 00	T _C = 25 °C		200	A	
Continuous Drain Current (T _J = 150 °C)	T _C = 125 °C	— I _D	140		
Pulsed Drain Current (t = 100 μs)		I _{DM}	800	^	
Avalanche Current	L = 0.1 mH	las	190		
Single Avalanche Energy ^a	L = 0.1 IIII	E _{AS}	1925	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	В	300 b	W	
waximum rower bissipation "	T _C = 125 °C	$ P_D$	125 ^b		
Operating Junction and Storage Temperature F	Range	T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	2.1	°C/W			
Junction-to-Case (Drain)	R _{thJC}	0.5	C/VV			

Notes

- a. Duty cycle $\leq 1 \%$.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	80	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	-	3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = 80 V, V_{GS} = 0 V, T_J = 125 °C	-	-	100	μA)	
		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 \text{ °C}$	-	-	2	mA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	200	-	-	Α	
Drain Source On State Besistance	D-	V _{GS} = 10 V, I _D = 30 A	-	0.0021	0.0027		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 30 \text{ A}$	-	0.0028	0.0036	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 30 A	-	90	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 50 V, f = 1 MHz	-	10500	-	pF	
Output Capacitance	C _{oss}		-	1650	-		
Reverse Transfer Capacitance	C _{rss}		-	75	-		
Total Gate Charge ^c	Q_g		-	168		nC	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	55	-		
Gate-Drain Charge ^c	Q_{gd}		-	23	-		
Gate Resistance	R_g	f = 1 MHz		2.3		Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	28	-		
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, R_L = 1.67 \Omega$	-	75	-	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 30 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	88	-		
Fall Time ^c	t _f		-	32	-		
Drain-Source Body Diode Ratings a	nd Characteri	stics ^b (T _C = 25 °C)					
Pulsed Current (t = 100 μs)	I _{SM}		-	-	800	Α	
Forward Voltage ^a	V _{SD}	I _F = 30 A, V _{GS} = 0 V	-	0.7	1.2	V	
Reverse Recovery Time	t _{rr}		-	118	-	ns	
Peak Reverse Recovery Charge	I _{RM(REC)}	$I_F = 30 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	5	10	Α	
Reverse Recovery Charge	Q_{rr}		-	305	-	μC	

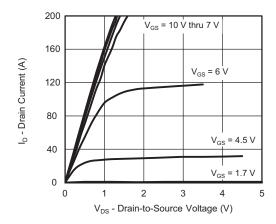
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

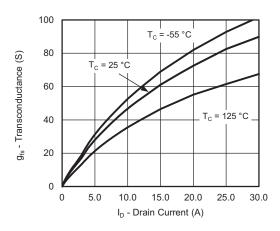
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



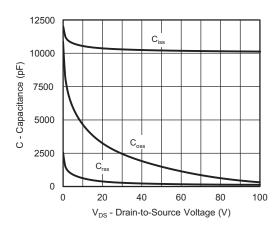
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



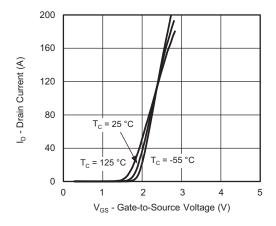
Output Characteristics



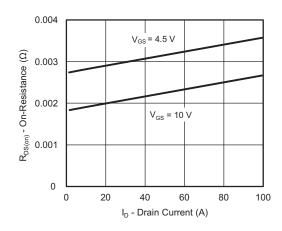
Transconductance



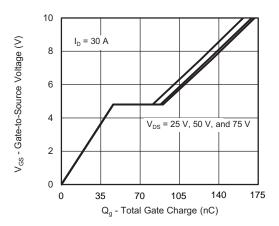
Capacitance



Transfer Characteristics



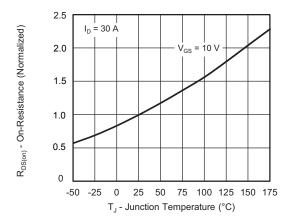
On-Resistance vs. Drain Current



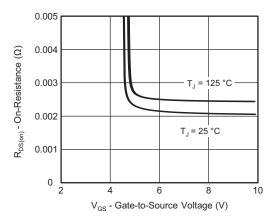
Gate Charge



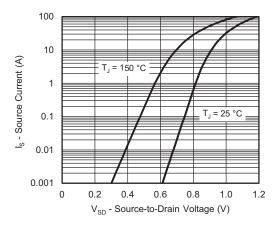
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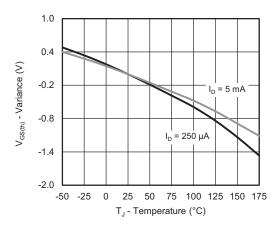
On-Resistance vs. Junction Temperature



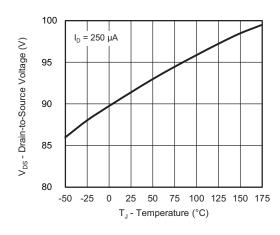
On-Resistance vs. Gate-to-Source Voltage



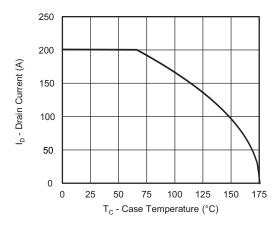
Source Drain Diode Forward Voltage



Threshold Voltage



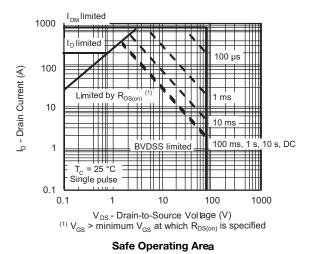
Drain Source Breakdown vs. Junction Temperature

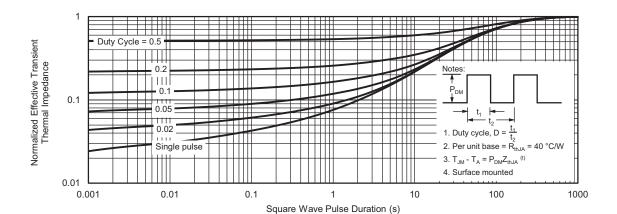


Current De-Rating



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)

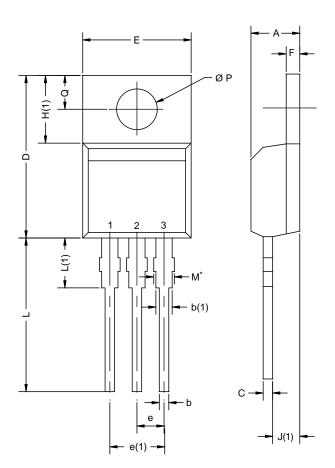




Normalized Thermal Transient Impedance, Junction-to-Ambient



TO-220AB



	MILLIM	IETERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	4.25	4.65	0.167	0.183	
b	0.69	1.01	0.027	0.040	
b(1)	1.20	1.73	0.047	0.068	
С	0.36	0.61	0.014	0.024	
D	14.85	15.49	0.585	0.610	
E	10.04	10.51	0.395	0.414	
е	2.41	2.67	0.095	0.105	
e(1)	4.88	5.28	0.192	0.208	
F	1.14	1.40	0.045	0.055	
H(1)	6.09	6.48	0.240	0.255	
J(1)	2.41	2.92	0.095	0.115	
L	13.35	14.02	0.526	0.552	
L(1)	3.32	3.82	0.131	0.150	
ØΡ	3.54	3.94	0.139	0.155	
Q	2.60	3.00	0.102	0.118	
ECN: X12-0208-Rev. N, 08-Oct-12 DWG: 5471					

Notes

 $^{^{*}}$ M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM





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